

S8550 S8550A M8550 MMT8550 SS8550 A6801

SOT—23 1. BASE 2. EMITTER 3. COLLECTOR



■FEATURES 特點

Low Frequency Power Amplifier 低頻功率放大 Suitable for Driver Stage If Small Motor 小馬達驅動 Complementary to 8050 与8050

■最大額定值(Ta=25℃)

CHARACTERISTIC 特性參數	Symbol 符號	Rating 額定値	Unit 單位
Collector-Base Voltage 集電極-基極電壓	V_{CBO}	-40 -25(A6801)	Vdc
Collect-Emitter Voltage 集電極-發射極電壓	V _{CEO}	-25 -18(A6801)	Vdc
Emitter-Base Voltage 發射極-基極電壓	$\mathrm{V}_{\mathrm{EBO}}$	-5.0	Vdc
Collector Current 集電極電流	Ic	-500(88550A,88550) -1000(M8550) -1200(MMT8550) -1500(888550) -1800(A6801)	mAdc
Collector Power Dissipation 集電極耗散功率	P _C	225	mW
Junction Temperature 結溫	T _j	150	°C
Storage Temperature Range 儲存溫度	T _{stg}	-55~150	°C

■DEVICE MARKING 打標

S8550	A=2TY.	S8550=2TY	M8550=Y2.	
MMT	°8550=Y2	SS8550=Y.2	A6801=6801	
■H _{FE}	RANGE	女大倍數分檔		
H _{FE}	(85~150), (120~220)		
	(200~300), (280~400)		

KEL 8550



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■ELECTRICAL CHARACTERISTICS 電特性

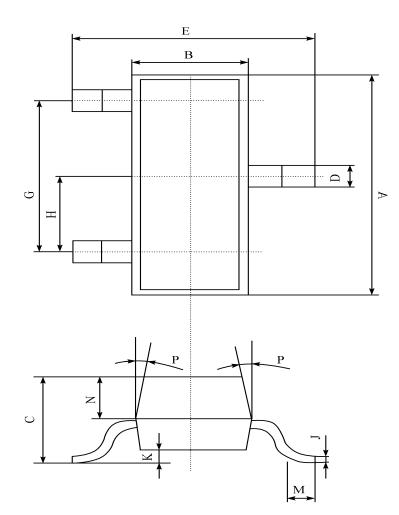
(T_A=25℃ unless otherwise noted 如無特殊說明,溫度爲 25℃)

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Characterstic 特性參數	Symbol 符號	Test Condition 測試條件	Min. 最小値	Typ. 典型值	Max. 最大値	Unit 單位
Collector Cutoff Current 集電極截止電流	I _{CBO}	V_{CB} =-30V, I_{E} =0			-0.1	μA
Emitter Cutoff Current 發射極截止電流	I _{EBO}	V_{EB} =-5V,I _C =0			-0.1	μA
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓	V _{(BR)CBOO}	I _C =-100 μ A (A6801)	-40 (-25)			V
Collector-Emitter Breakdown Voltage 集電極-發射極擊穿電壓	V _{(BR)CEO}	I _C =-10mA (A6801)	-25 (-18)			V
Emitter-Base Breakdown Voltage 發射極-基極擊穿電壓	V _{(BR)EBO}	I_{E} =-100 μ A	-5			V
	$H_{FE}(1)$	V _{CE} =-1V,I _C =-100mA	85		400	
DC Current Gain 直流電流增益	H _{FE} (2)	$V_{CE} = -1V,$ $I_{C} = -1800 \text{ mA}(\text{A6801})$ $I_{C} = -800 \text{ mA}$ (SS8550, MMT8550, M8550) $I_{C} = -500 \text{ mA}(\text{S8550})$ $I_{C} = -500 \text{ mA}(\text{S8550A})$	50 40 40 30			
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-0.6	V
Base-Emitter Voltage 基極-發射極電壓	V_{BE}	V _{CE} =-1V,I _C =-10mA		-0.8	-1.0	V
Transition Frequency 特徵頻率	f _T	V _{CE} =-5V,I _C =-10mA	100	120		MHz
Collector Output Capacitance 輸出電容	C _{ob}	V _{CB} =-10V,I _E =0,f=1MHz		13	30	pF



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■DIMENSION 外形封裝尺寸



序號	數值及公差	
Α	2.90 ± 0.10	
В	1.30 ± 0.10	
С	1.00 ± 0.10	
D	0.40 ± 0.10	
Е	2.40 ± 0.20	
G	1.90 ± 0.10	
Н	0.95 ± 0.05	
J	0.13 ± 0.05	
K	0.00-0.10	
М	≥0.2	
N	0.60 ± 0.10	
Р	$7\pm2°$	

This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website http://www.takcheong.com.

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